

Silicon NPN Power Transistors

2SC4924

DESCRIPTION

- With TO-3PML package
- High breakdown voltage, high reliability.
- High speed

APPLICATIONS

- Very high-definition CRT display
- Horizontal deflection output applications

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |

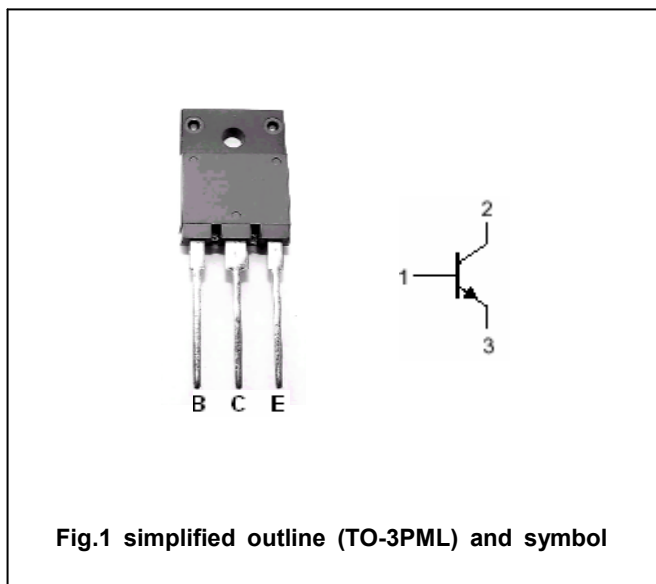


Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings(Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|-----------------------------|----------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | 1500 | V |
| V _{CEO} | Collector-emitter voltage | Open base | 800 | V |
| V _{EBO} | Emitter-base voltage | Open collector | 6 | V |
| I _C | Collector current | | 10 | A |
| I _{CM} | Collector current-peak | | 25 | A |
| P _C | Collector power dissipation | T _C =25°C | 70 | W |
| | | | 3 | |
| T _j | Junction temperature | | 150 | °C |
| T _{stg} | Storage temperature | | -55~150 | °C |

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{CEO(SUS)} | Collector-emitter sustaining voltage | I _C =100mA; I _B =0 | 800 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =8A; I _B =2 A | | | 5 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =8A; I _B =2 A | | | 1.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =800V; I _E =0 | | | 10 | μA |
| I _{CES} | Collector cut-off current | V _{CE} =1500V; R _{BE} =0 | | | 1 | mA |
| h _{FE-1} | DC current gain | I _C =1A; V _{CE} =5V | 8 | | | |
| h _{FE-2} | DC current gain | I _C =8A; V _{CE} =5V | 4 | | 8 | |

Switching times

| | | | | | | |
|------------------|--------------|--|--|-----|-----|----|
| t _{stg} | Storage time | I _C =6A; R _L =33.3Ω I _{B1} =1.2A; - I _{B2} =2.4A V _{CC} =200V | | | 3 | μs |
| t _f | Fall time | | | 0.1 | 0.2 | μs |

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PACKAGE OUTLINE

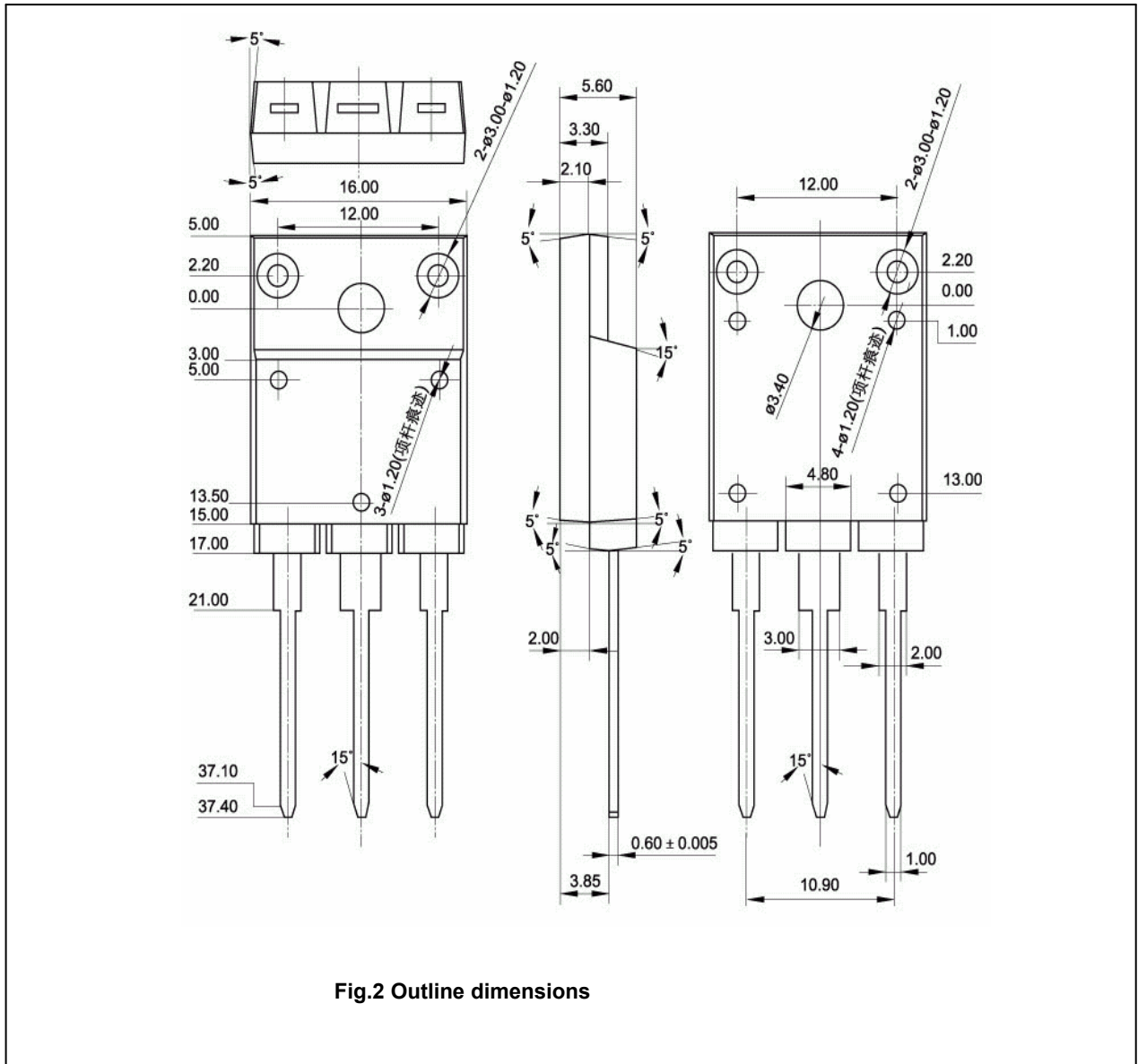


Fig.2 Outline dimensions

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